

# PATENT ABSTRACTS OF JAPAN

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(54) SEMICONDUCTOR PHOTOELECTRIC DEVICE AND ITS MANUFACTURING METHOD

(57)Abstract:

PURPOSE: By obtaining the Si phototransistor of which junction depth of the optical base area is more shallower than that just under the emitter area, the spectral sensitivity of the peak wavelength 9000  $\text{\AA}$ ; and the dark current shall be reduced.

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## LEGAL STATUS.

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